

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1973	(716/4).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:52
S2	1477	(716/5).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:52
S3	1267	(716/1).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:52
S4	0	(716/4).ccls. and (FET) and (threshold adj distance) and ((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:55
S5	1	(716/5).ccls. and (FET) and (threshold adj distance) and ((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:55
S6	0	(716/1).ccls. and (FET) and (threshold adj distance) and ((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:56
S7	1	("716"/\$).ccls. and (FET) and (threshold adj distance) and ((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:56
S8	1	(FET) and (threshold adj distance) and ((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:58
S9	2	(FET) and (threshold adj distance) and (well adj edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 11:59
S10	6	((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:04

S11	2	("5875117").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:05
S12	2	("20030145296").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:18
S13	0	(singnal adj integrity) and (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:19
S14	232	(signal adj integrity) and (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:24
S15	2	((signal adj integrity) adj analysis) same (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:20
S16	7	((signal adj integrity) adj analysis) and (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:20
S17	9	(signal adj integrity) same (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:27
S18	2	(threshold adj distance) same (well) same (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:28
S19	2	(threshold adj distance) and ((well) same (FET))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:29
S20	366	((threshold) same (separation or gap or distance)) and ((well) same (FET))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:31

S21	3	((threshold) same (separation or gap or distance)) and ((well adj edge) same (FET))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:31
S22	9	(well adj edge) and (active adj (area or region)) and (FET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 12:56
S23	2	(FET or ((field adj effect) adj transistor\$2)) same ((signal adj integrity) adj analysis)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 13:08
S24	12	(FET or ((field adj effect) adj transistor\$2)) same (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 13:08
S25	6	((well adj proximity) adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 13:22
S26	4886922	(well proximity effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 13:22
S27	6	("well proximity effect")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 17:05
S28	1	("well proximity effect") and (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 14:09
S29	3	(well adj edge) and (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/15 14:09
S30	18	(signal adj integrity) same (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 16:39

S31	110	(nois\$2) near (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 12:40
S32	57	((signal adj integrity) adj analysis)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:18
S33	0	((signal adj integrity) adj analysis) same (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:19
S34	4	((signal adj integrity) adj analysis) and (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:42
S35	2	((signal adj integrity) adj analysis) same (FET or ((field adj effect) adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:45
S36	8	((signal adj integrity) adj analysis) and (FET or ((field adj effect) adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:48
S37	8	((signal adj integrity) adj analy\$5) and (FET or ((field adj effect) adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:50
S38	12	(signal adj integrity) same (FET or ((field adj effect) adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:57
S39	18	(signal adj integrity) same (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 14:57
S40	1	("well proximity effect") and (threshold adj distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/30 17:06